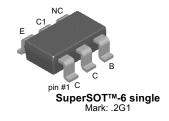


FMBSA56

PNP General Purpose Amplifier

- This device is designed for general purpose amplifier applications at collector currents to 300 mA.
- · Sourced from Process 73.



Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	-80	V
V _{CBO}	Collector-Base Voltage	-80	V
V _{EBO}	Emitter-Base Voltage	-4.0	V
I _C	Collector Current - Continuous	-500	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units	
Off Characte	Off Characteristics					
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage *	I _C = -1.0mA, I _B = 0	-80		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0$	-80			
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-4.0		V	
I _{CEO}	Collector Cut-off Current	V _{CE} = -60V, I _B = 0		-0.1	μΑ	
I _{CBO}	Collector Cut-off Current	V _{CB} = -80V, I _E = 0		-0.1	μΑ	
On Characte	eristics		•			
h _{FE}	DC Current Gain	I _C = -10mA, V _{CE} = -1.0V	100			
		$I_C = -100 \text{mA}, V_{CE} = -1.0 \text{V}$	100			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -100mA, I _B = -10mA		-0.25	V	
V _{BE(on)}	Base-Emitter On Voltage	I _C = -100mA, V _{CE} = -1.0V		-1.2	V	
	l Characteristics		•	•	•	
f _T	Current Gain Bandwidth Product	I _C = -10mA, V _{CE} = -2.0V, f = 100MHz	50		MHz	

^{*} Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

Thermal Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation *	700	mW
R _{0JA}	Thermal Resistance, Junction to Ambient, total	180	°C/W

^{*} Device mounted on a 1 in 2 pad of 2 oz copper.

Typical Characteristics

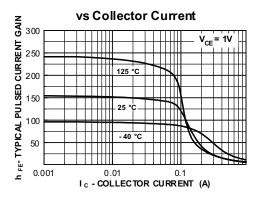


Figure 1. Typical Pulsed Current Gain vs Collector Current

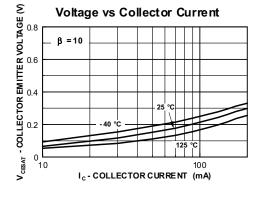


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

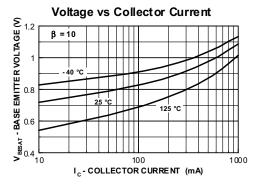


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

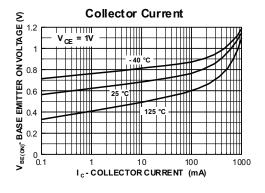


Figure 4. Base-Emitter On Voltage vs Collector Current

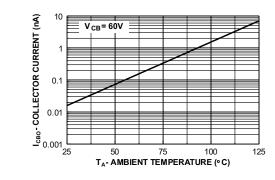


Figure 5. Collector Cutoff Current vs Ambient Temperature

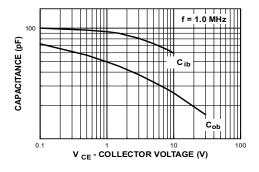


Figure 6. Collector Saturation Region

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Typical Characteristics (Continued)

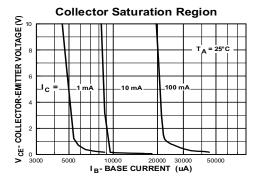


Figure 7. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

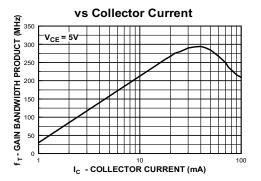
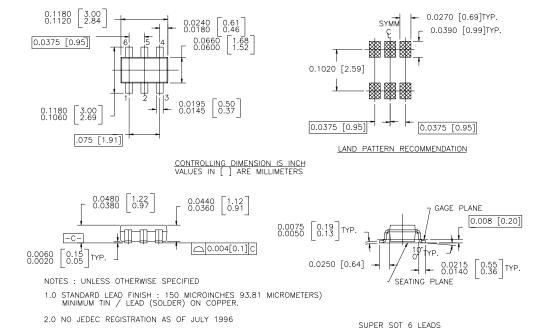


Figure 8. Input and Output Capacitance vs Reverse Voltage

Package Dimensions

SuperSOT™-6



Dimensions in Millimeters

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E ² CMOS™	I ² C™	MSXPro™	Quiet Series™	TINYOPTO™
EnSigna™	i-Lo™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™	И	OPTOLOGIC [®]	μSerDes™	UltraFET [®]
Across the board. Around the world.™		OPTOPLANAR™	SILENT SWITCHER®	VCX™
The Power Franchis	$e^{ ext{ iny R}}$	PACMAN™	SMART START™	
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